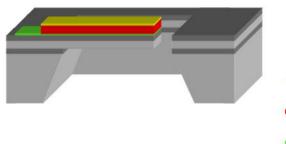


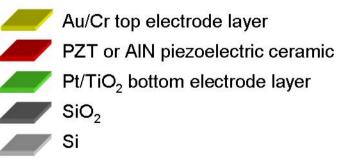
Starting point: Oxidised silicon-on-insulator wafer (SOI).

Backside opening by wet etch, Pt bottom electrode by sputtering, Piezoelectric layer by CSD, sputtering or PLD, Au/Cr top electrode by vapour deposition and lift off patterning.

Pattering of piezoelectric layer by wet etch, Back side cavity removal by wet etch.



Release by reactive ion etch.



Piezoelectric MEMS devices are produced through a series of deposition and etching steps.